

FDMS8660AS

N-Channel PowerTrench® SyncFET™

30V, 49A, 2.1mΩ

Features

- Max $r_{DS(on)}$ = 2.1mΩ at $V_{GS} = 10V$, $I_D = 28A$
- Max $r_{DS(on)}$ = 3.1mΩ at $V_{GS} = 4.5V$, $I_D = 22A$
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- SyncFET Schottky Body Diode
- MSL1 robust package design
- RoHS Compliant

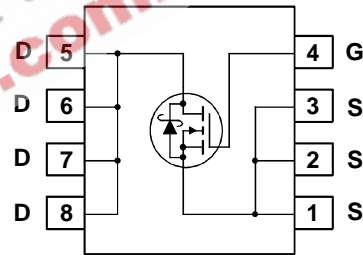
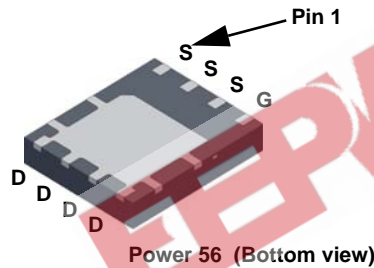


General Description

The FDMS8660AS has been designed to minimize losses in power conversion application. Advancements in both silicon and package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance. This device has the added benefit of an efficient monolithic Schottky body diode.

Applications

- Synchronous Rectifier for DC/DC Converters
- Notebook Vcore/ GPU low side switch
- Networking Point of Load low side switch
- Telecom secondary side rectification



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated Value	Units
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	49	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	179	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	28	
	-Pulsed	200	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	726	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	104	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8660AS	FDMS8660AS	Power 56	13"	12mm	3000units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 1\text{mA}, V_{GS} = 0\text{V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{mA}$, referenced to 25°C		27		$\text{mV}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$			500	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 1\text{mA}$	1.0	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 10\text{mA}$, referenced to 25°C		-5		$\text{mV}/^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 28\text{A}$		1.7	2.1	m Ω
		$V_{GS} = 4.5\text{V}, I_D = 22\text{A}$		2.3	3.1	
		$V_{GS} = 10\text{V}, I_D = 28\text{A}, T_J = 125^\circ\text{C}$		2.3	3.1	
g_{FS}	Forward Transconductance	$V_{DD} = 10\text{V}, I_D = 28\text{A}$		167		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	4410	5865	pF
C_{oss}	Output Capacitance		2305	3065	pF
C_{rss}	Reverse Transfer Capacitance		185	280	pF
R_g	Gate Resistance		1.2		Ω

Switching Characteristics

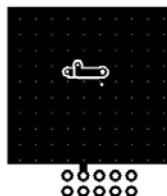
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{V}, I_D = 28\text{A}, V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$	16	29	ns
t_r	Rise Time		8	16	ns
$t_{d(off)}$	Turn-Off Delay Time		42	68	ns
t_f	Fall Time		5	10	ns
Q_g	Total Gate Charge		$V_{GS} = 0\text{V}$ to 10V	59	83
Q_g	Total Gate Charge	$V_{GS} = 0\text{V}$ to 4.5V	30	42	nC
Q_{gs}	Gate to Source Charge	$V_{DD} = 15\text{V}, I_D = 28\text{A}$	12		nC
Q_{gd}	Gate to Drain "Miller" Charge		5.2		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 2\text{A}$ (Note 3)		0.4	0.7	V
t_{rr}	Reverse Recovery Time	$I_F = 28\text{A}, di/dt = 300\text{A}/\mu\text{s}$		46	74	ns
Q_{rr}	Reverse Recovery Charge			67	108	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $50^\circ\text{C}/\text{W}$ when mounted on a 1in^2 pad of 2 oz copper.



b. $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Starting $T_J = 25^\circ\text{C}$, $L = 3\text{mH}$, $I_{AS} = 22\text{A}$, $V_{DD} = 30\text{V}$, $V_{GS} = 10\text{V}$.

3. Pulse Test: Pulse Width $< 300\mu\text{s}$, Duty cycle $< 2.0\%$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

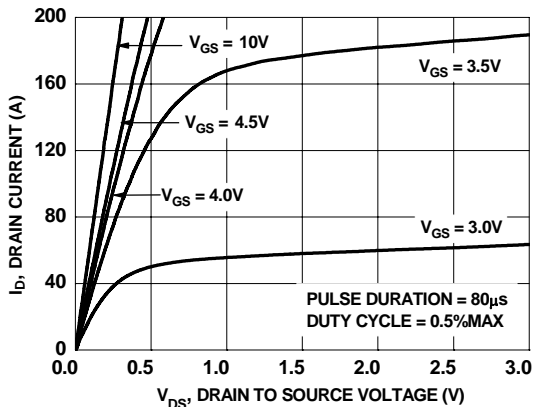


Figure 1. On-Region Characteristics

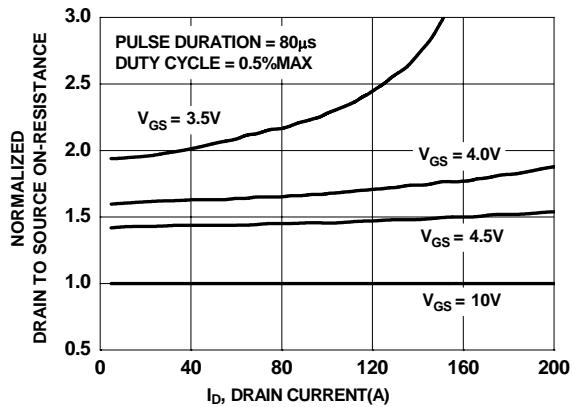


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

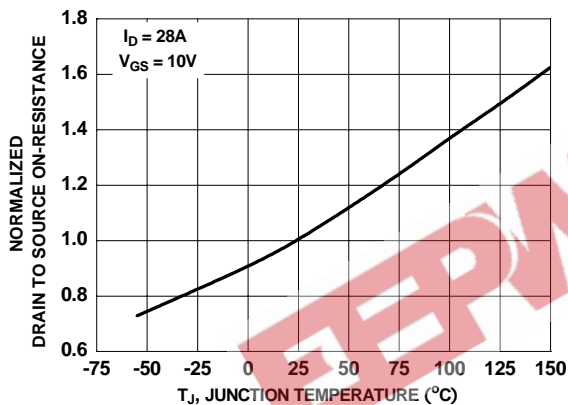


Figure 3. Normalized On-Resistance vs Junction Temperature

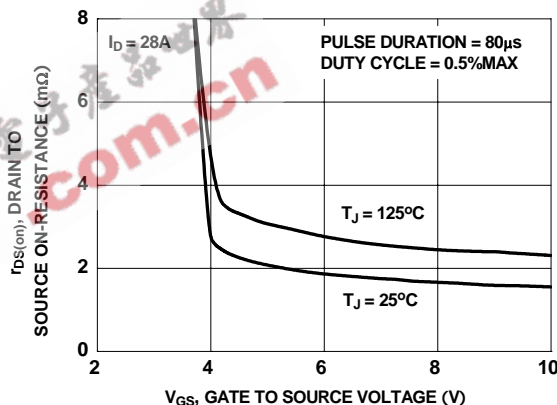


Figure 4. On-Resistance vs Gate to Source Voltage

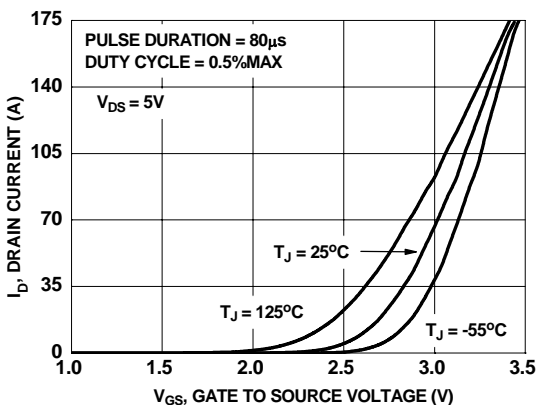


Figure 5. Transfer Characteristics

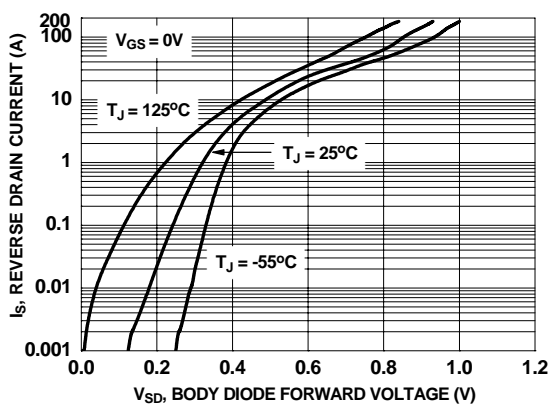


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

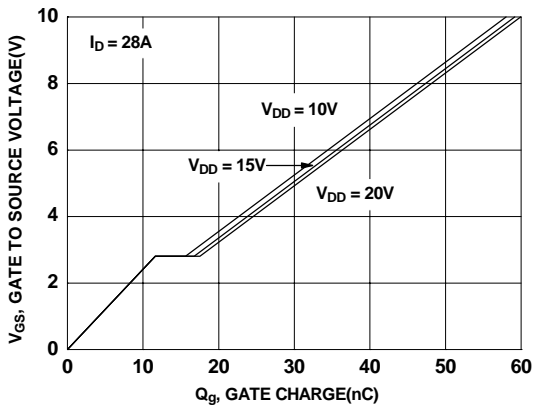


Figure 7. Gate Charge Characteristics

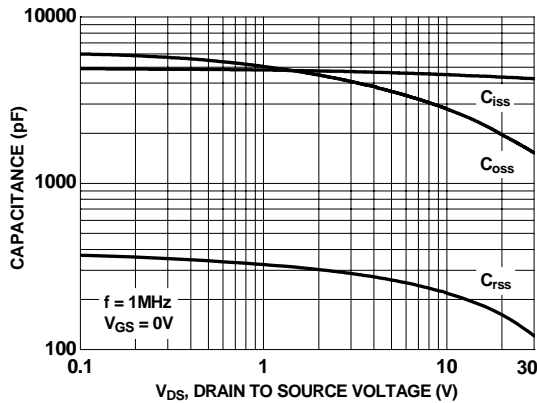


Figure 8. Capacitance vs Drain to Source Voltage

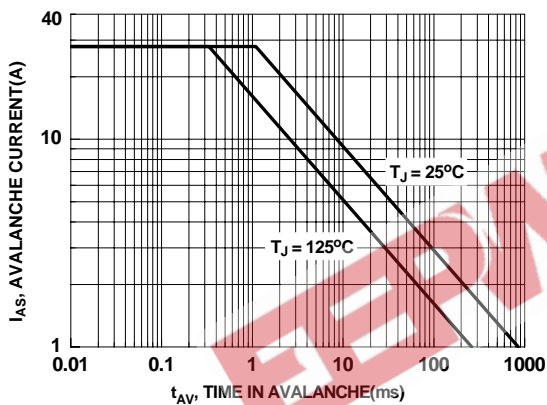


Figure 9. Unclamped Inductive Switching Capability

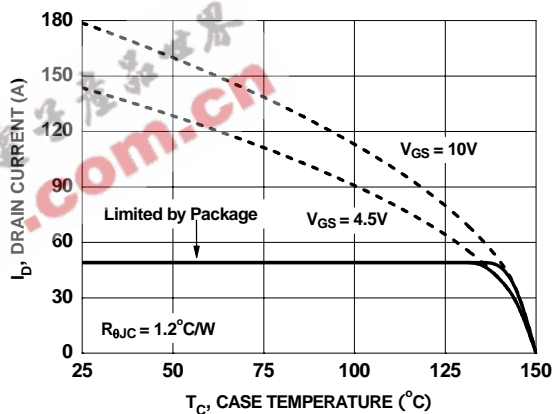


Figure 10. Maximum Continuous Drain Current vs Case Temperature

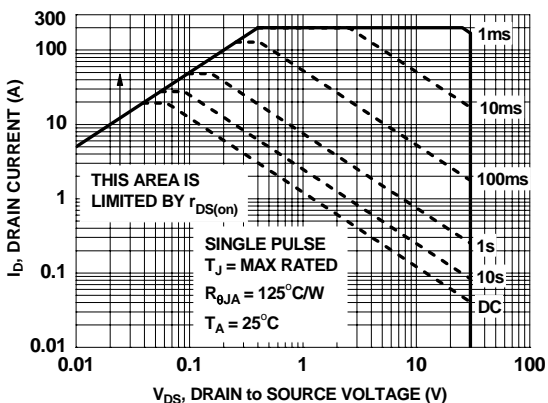


Figure 11. Forward Bias Safe Operating Area

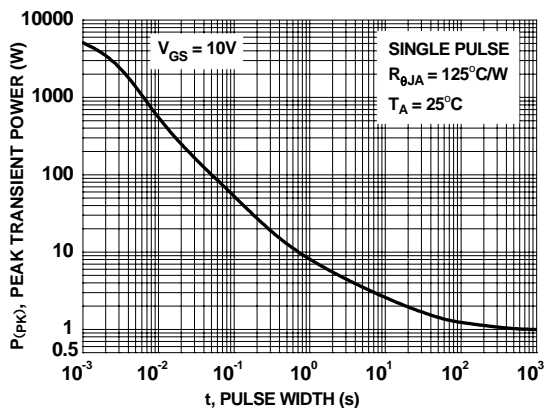


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

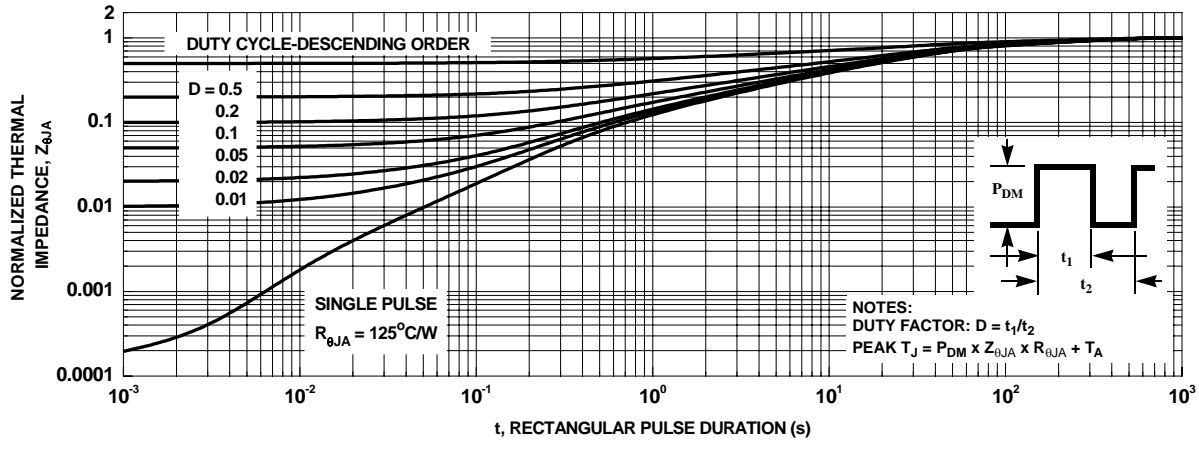


Figure 13. Transient Thermal Response Curve

EEPW 电子产品世界 .com.cn

Typical Characteristics (continued)

SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 14 shows the reverse recovery characteristic of the FDMS8660AS.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

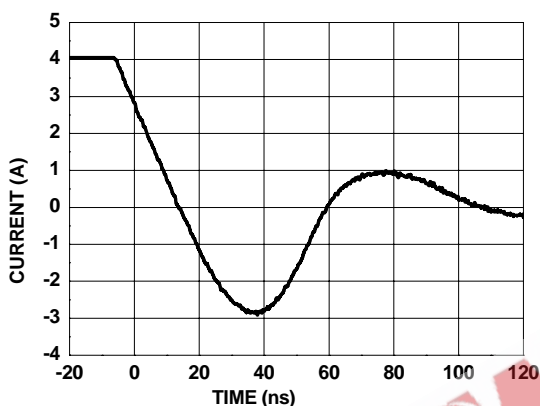


Figure 14. FDMS8660AS SyncFET Body Diode Reverse Recovery Characteristics

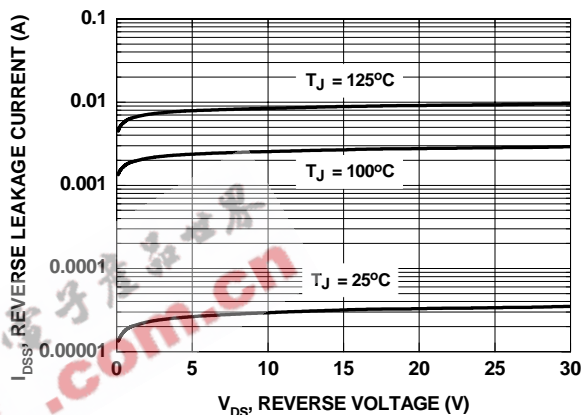
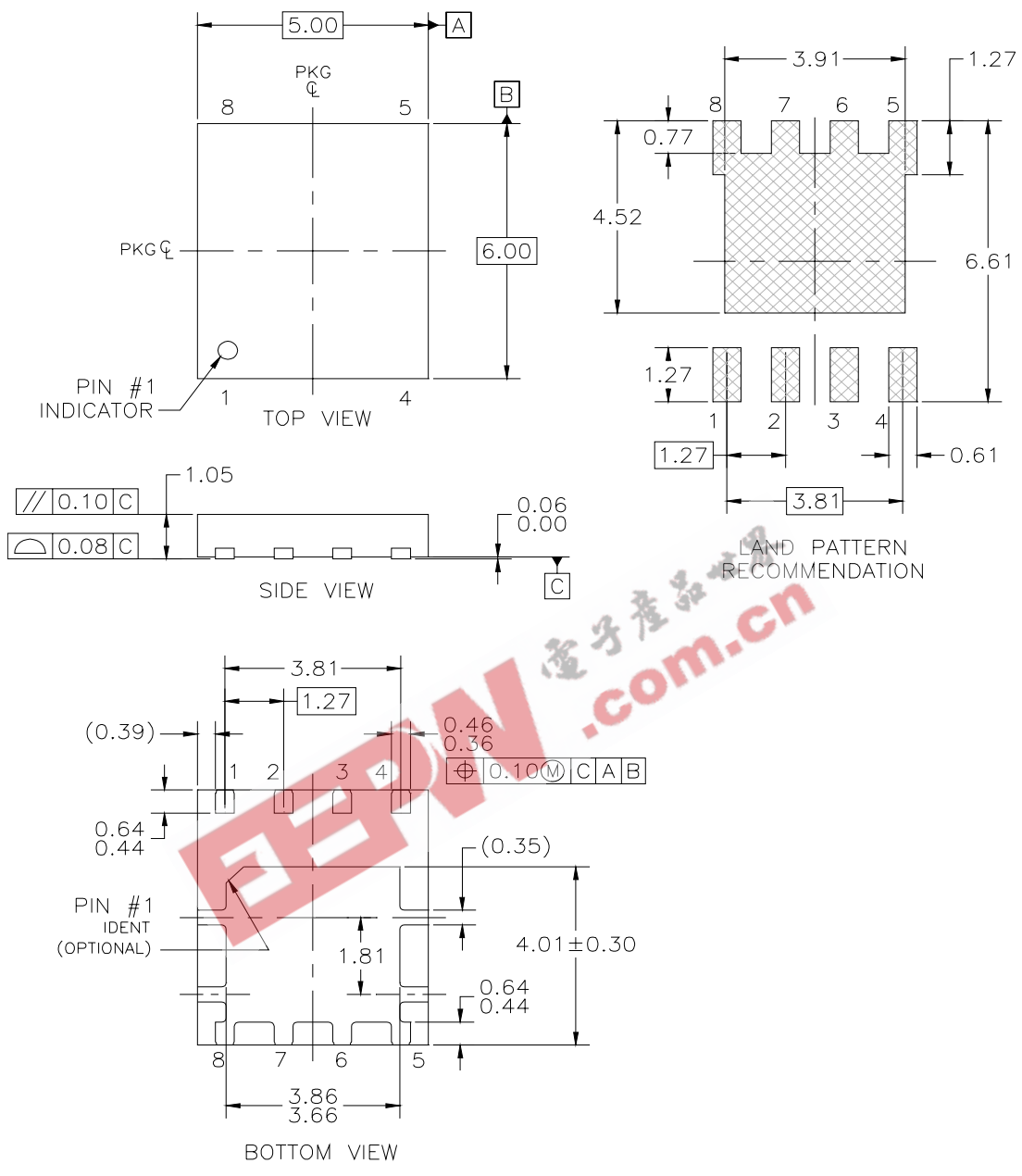


Figure 15. SyncFET Body Diode Reverse Leakage vs Drain to Source Voltage



- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 - B) NO JEDEC REFERENCE AS OF FEBRUARY 2006
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994

PQFN08AREVA



TRADEMARKS

The following are registered and unregistered trademarks and service marks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE [®]	Green FPST [™]	Power247 [®]	SuperSOT [™] -8
Build it Now [™]	Green FPST [™] e-Series [™]	POWEREDGE [®]	SyncFET [™]
CorePLUS [™]	GTO [™]	Power-SPM [™]	The Power Franchise [®]
CROSSVOLT [™]	<i>i-Lo</i> [™]	PowerTrench [®]	the power franchise
CTL [™]	IntelliMAX [™]	Programmable Active Droop [™]	TinyBoost [™]
Current Transfer Logic [™]	ISOPLANAR [™]	QFET [®]	TinyBuck [™]
EcoSPARK [®]	MegaBuck [™]	QS [™]	TinyLogic [®]
F [®]	MICROCOUPLER [™]	QT Optoelectronics [™]	TINYOPTO [™]
Fairchild [®]	MicroFET [™]	Quiet Series [™]	TinyPower [™]
Fairchild Semiconductor [®]	MicroPak [™]	RapidConfigure [™]	TinyPWM [™]
FACT Quiet Series [™]	MillerDrive [™]	SMART START [™]	TinyWire [™]
FACT [®]	Motion-SPM [™]	SPM [®]	μSerDes [™]
FAST [®]	OPTOLOGIC [®]	STEALTH [™]	UHC [®]
FastvCore [™]	OPTOPLANAR [®]	SuperFET [™]	UniFET [™]
FPS [™]	 [®]	SuperSOT [™] -3	VCX [™]
FRFET [®]	PDP-SPM [™]	SuperSOT [™] -6	
Global Power Resource SM	Power220 [®]		

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild Semiconductor. The datasheet is printed for reference information only.

Rev. I31